IIT ROORKEE

NPTEL ONLINE CERTIFICATION COURSE

MICROELECTRONICS: DEVICES TO CIRCUITS

BIPOLAR JUNCTION TRANSISTOR: MODES OF OPERATION

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- The concentration $n_p(0)$ will be proportional to $e^{\frac{v_{BE}}{v_T}}$.

$$n_p(0) = n_{p0} e^{\frac{v_{BE}}{v_T}}$$

- The electron diffusion current I_n is directly proportional to the slope of the straight line concentration profile.

$$I_n = A_E q D_n \frac{d_{n_p(X)}}{dx}$$

$$I_n = A_E q D_n \left(-\frac{n_p(0)}{W} \right)$$

A_E Cross-sectional area of the base-emitter junction

q Electron charge

D_n Electron diffusivity in the base

W Effective width of the base

Source: Microelectronics Circuits, Sedra and Smith, Fifth edition

Collector current

$$I_C = I_n$$

$$I_C = I_S e^{\frac{v_{BE}}{V_T}}$$

$$I_S = A_E D_n q \frac{n_{p0}}{W}$$

$$n_{p0} = \frac{n_i^2}{N_A}$$

$$I_s = \frac{A_E q D_n n_i^2}{N_A W}$$

I_s Saturation current

I_C Collector Current

n_i Intrinsic carrier density

N_A Doping Concentration

I_s is doubling for every 5°C rise in temperature

Source: Microelectronics Circuits, Sedra and Smith, Fifth edition

Base current

$$I_B = \frac{I_C}{\beta}$$

β Common-emitter current gain

$$I_B = \frac{I_S}{\beta} e^{\frac{v_{BE}}{v_T}}$$

- For modern npn transistor β is in the range 50 to200.
- β is highly influenced by, width of base region W and relative doping of base region and emitter region $\frac{N_A}{N_D}$.

Source: Microelectronics Circuits, Sedra and Smith, Fifth edition

Emitter current

$$I_E = I_c + I_B$$

$$I_E = \frac{\beta + 1}{\beta} I_C$$

$$I_E = \frac{\beta + 1}{\beta} I_S e^{\frac{v_{BE}}{v_T}}$$

$$I_C = \alpha I_E$$

$$\alpha = \frac{\beta}{\beta + 1} \qquad \beta = \frac{\alpha}{1 - \alpha}$$

$$I_E = \frac{I_S}{\alpha} e^{\frac{v_{BE}}{v_T}}$$

α Common base current gain

Source: Microelectronics Circuits, Sedra and Smith, Fifth edition

Large signal equivalent –circuit model of npn BJT

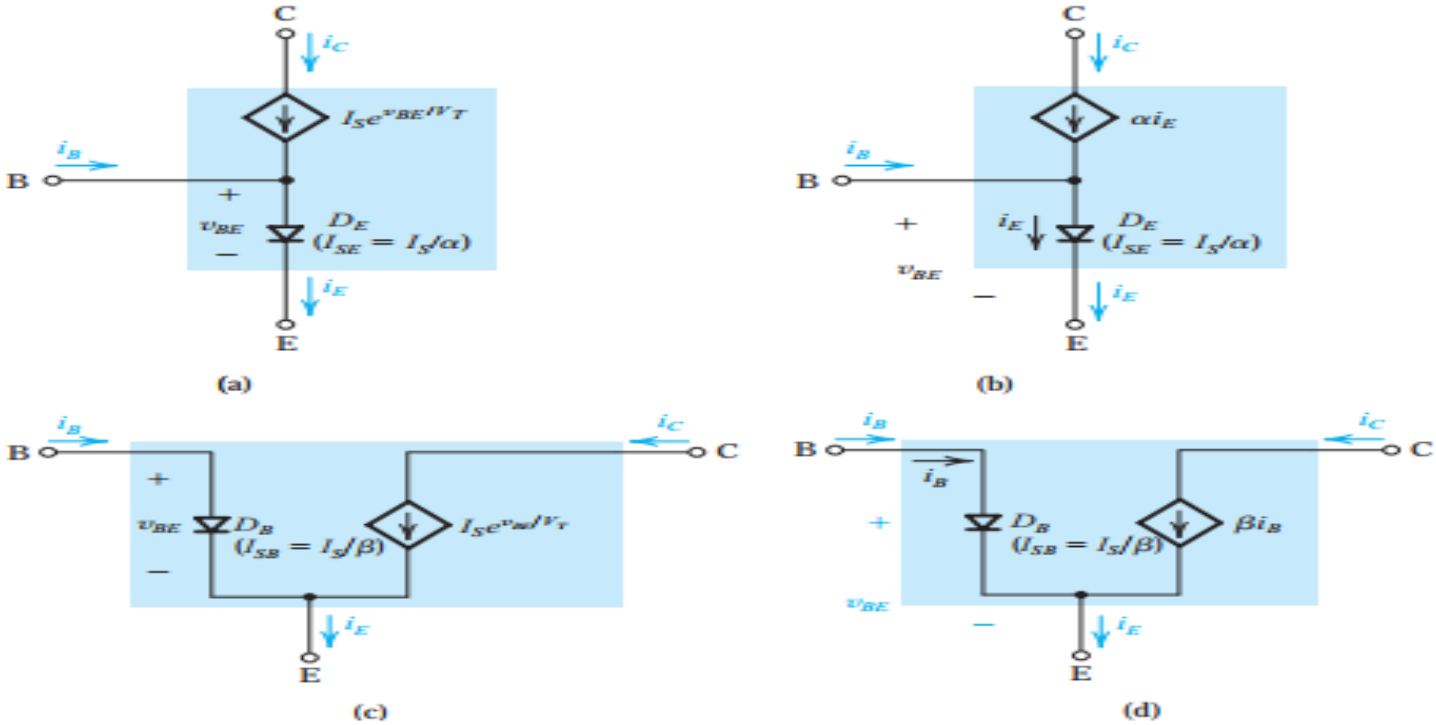


Fig.6. Large signal equivalent –circuit model for npn transistor in active mode

Source: Microelectronics Circuits, Sedra and Smith, Fifth edition

Recapitulation

- Presented first order model of npn transistor operated in active mode.
- The forward bias voltage v_{BE} causes an exponential related current I_C to flow in the collector terminal.
- The collector current I_C is independent of the value of the collector voltage as long as collector- base region junction remains reverse biased.
- In the active mode the collector terminal behaves as an ideal constant-current source.
- The base current I_B is a factor 1/β of the collector current.

Source: Microelectronics Circuits, Sedra and Smith, Fifth edition

Thank You